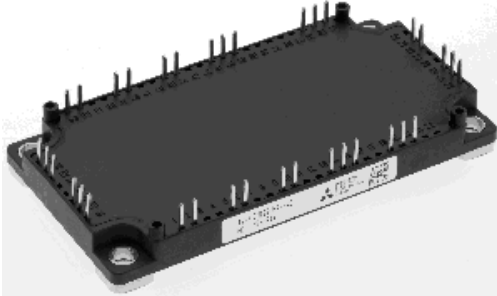


< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE



CIB (Converter+Inverter+Chopper Brake)

Collector current I_C **75 A**
 Collector-emitter voltage V_{CES} **1200 V**
 Maximum junction temperature T_{jmax} **175 °C**

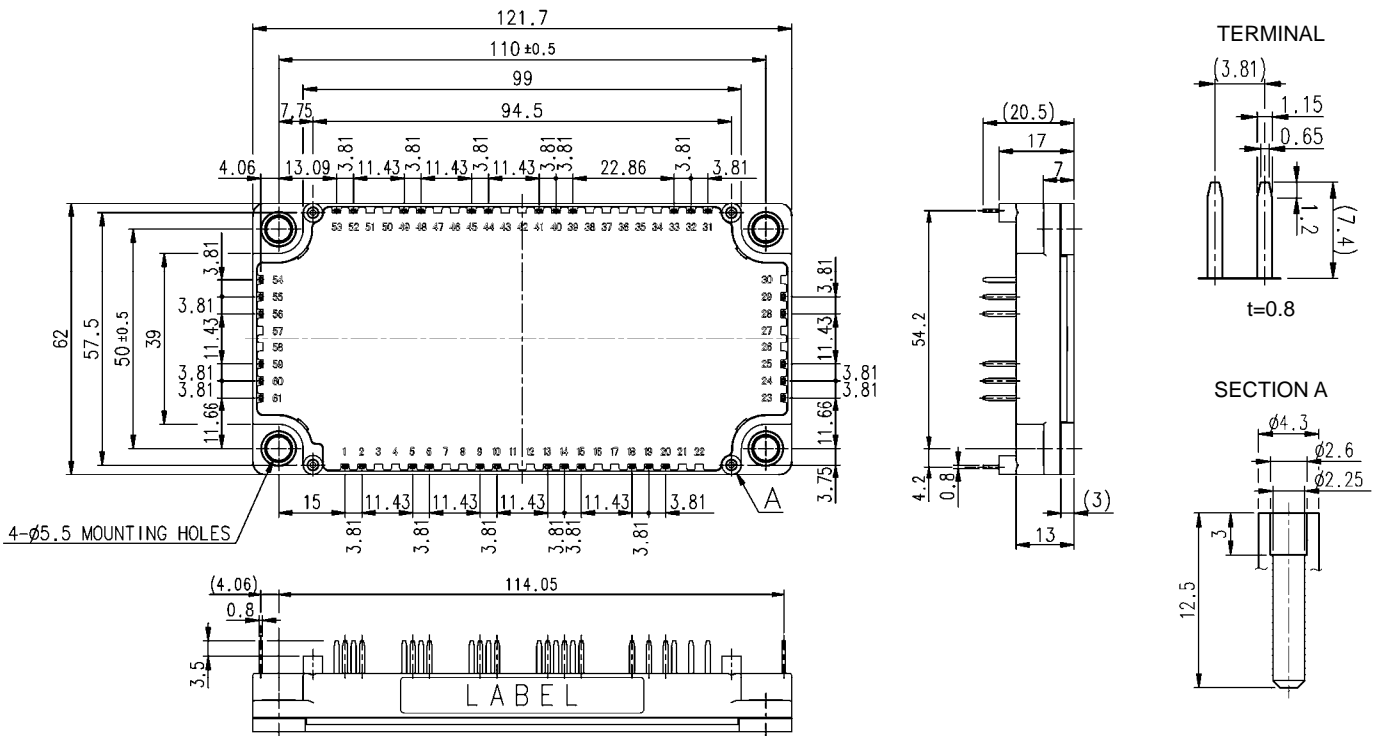
- Flat base Type
- Copper base plate
- Tin plating pin terminals
- RoHS Directive compliant
- Recognized under UL1557, File E323585

APPLICATION

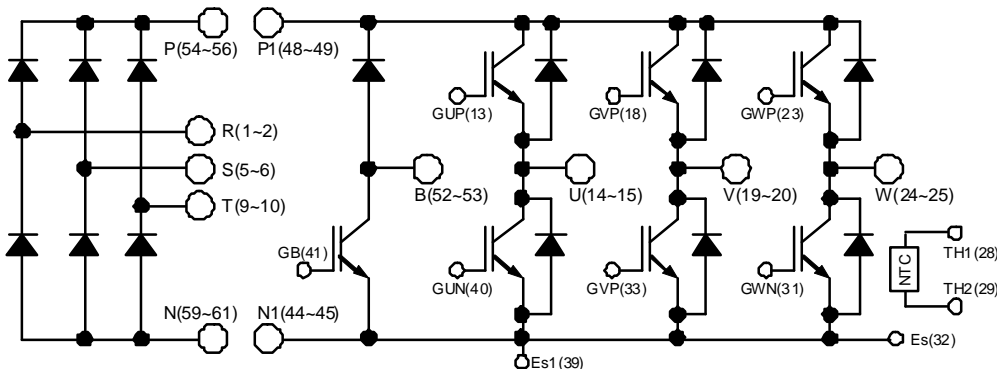
AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



INTERNAL CONNECTION



Caution: Each (two or three) pin terminal of P/N/P1/N1/U/V/W/B/R/S/T is connected in the module, but should use all each three pins for the external wiring.

Tolerance otherwise specified

| Division of Dimension | Tolerance |
|-----------------------|-----------|
| 0.5 to 3 | ±0.2 |
| over 3 to 6 | ±0.3 |
| over 6 to 30 | ±0.5 |
| over 30 to 120 | ±0.8 |
| over 120 to 400 | ±1.2 |

The tolerance of size between terminals is assumed to be ±0.4.

< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/DIODE

| Symbol | Item | Conditions | Rating | Unit |
|--------------------------|------------------------------|---------------------------------------|--------|------|
| V _{CES} | Collector-emitter voltage | G-E short-circuited | 1200 | V |
| V _{GES} | Gate-emitter voltage | C-E short-circuited | ± 20 | V |
| I _C | Collector current | DC, T _C =122 °C (Note2, 4) | 75 | A |
| I _{CRM} | | Pulse, Repetitive (Note3) | 150 | |
| P _{tot} | Total power dissipation | T _C =25 °C (Note2, 4) | 600 | W |
| I _E (Note1) | Emitter current | (Note2) | 75 | A |
| I _{ERM} (Note1) | | Pulse, Repetitive (Note3) | 150 | |
| T _{jm ax} | Maximum junction temperature | Instantaneous event (overload) | 175 | °C |

BRAKE PART IGBT/DIODE

| Symbol | Item | Conditions | Rating | Unit |
|--------------------|---------------------------------|---------------------------------------|--------|------|
| V _{CES} | Collector-emitter voltage | G-E short-circuited | 1200 | V |
| V _{GES} | Gate-emitter voltage | C-E short-circuited | ± 20 | V |
| I _C | Collector current | DC, T _C =125 °C (Note2, 4) | 50 | A |
| I _{CRM} | | Pulse, Repetitive (Note3) | 100 | |
| P _{tot} | Total power dissipation | T _C =25 °C (Note2, 4) | 425 | W |
| V _{R RM} | Repetitive peak reverse voltage | G-E short-circuited | 1200 | V |
| I _F | Forward current | (Note2) | 50 | A |
| I _{FRM} | | Pulse, Repetitive (Note3) | 100 | |
| T _{jm ax} | Maximum junction temperature | Instantaneous event (overload) | 175 | °C |

CONVERTER PART DIODE

| Symbol | Item | Conditions | Rating | Unit |
|--------------------|---------------------------------|---|--------|------------------|
| V _{R RM} | Repetitive peak reverse voltage | - | 1600 | V |
| E _a | Recommended AC input voltage | RMS | 440 | V |
| I _O | DC output current | 3-phase full wave rectifying, T _C =125 °C (Note4) | 75 | A |
| I _{FSM} | Surge forward current | The sine half wave 1 cycle peak value, f=60 Hz, non-repetitive | 750 | A |
| I ² t | Current square time | Value for one cycle of surge current | 2340 | A ² s |
| T _{jm ax} | Maximum junction temperature | Instantaneous event (overload) | 150 | °C |

MODULE

| Symbol | Item | Conditions | Rating | Unit |
|--------------------|--------------------------------|---|------------|------|
| V _{isol} | Isolation voltage | Terminals to base plate, RMS, f=60 Hz, AC 1 min | 2500 | V |
| T _{C max} | Maximum case temperature | (Note4) | 125 | °C |
| T _{j op} | Operating junction temperature | Continuous operation (under switching) | -40 ~ +150 | °C |
| T _{stg} | Storage temperature | - | -40 ~ +125 | |

MECHANICAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|----------------|------------------------|---------------------------------|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| M _s | Mounting torque | Mounting to heat sink M 5 screw | 2.5 | 3.0 | 3.5 | N·m |
| d _s | Creepage distance | Terminal to terminal | 6.47 | - | - | mm |
| | | Terminal to base plate | 14.27 | - | - | |
| d _a | Clearance | Terminal to terminal | 6.47 | - | - | mm |
| | | Terminal to base plate | 12.33 | - | - | |
| m | mass | - | - | 300 | - | g |
| e _c | Flatness of base plate | On the centerline X, Y (Note5) | ±0 | - | +100 | µm |

< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/DIODE

| Symbol | Item | Conditions | Limits | | | Unit | |
|------------------------------------|--------------------------------------|--|------------------------|------|------|------|---|
| | | | Min. | Typ. | Max. | | |
| I _{CES} | Collector-emitter cut-off current | V _{CE} =V _{CES} , G-E short-circuited | - | - | 1.0 | mA | |
| I _{GES} | Gate-emitter leakage current | V _{GE} =V _{GES} , C-E short-circuited | - | - | 0.5 | μA | |
| V _{GE(th)} | Gate-emitter threshold voltage | I _C =7.5 mA, V _{CE} =10 V | 5.4 | 6.0 | 6.6 | V | |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =75 A ^(Note6) , V _{GE} =15 V, (Terminal) | T _j =25 °C | - | 1.80 | 2.25 | V |
| | | | T _j =125 °C | - | 2.00 | - | |
| | | | T _j =150 °C | - | 2.05 | - | |
| | | I _C =75 A ^(Note6) , V _{GE} =15 V, (Chip) | T _j =25 °C | - | 1.70 | 2.15 | V |
| | | | T _j =125 °C | - | 1.90 | - | |
| | | | T _j =150 °C | - | 1.95 | - | |
| C _{ies} | Input capacitance | V _{CE} =10 V, G-E short-circuited | - | - | 7.5 | nF | |
| C _{oes} | Output capacitance | | - | - | 1.5 | | |
| C _{res} | Reverse transfer capacitance | | - | - | 0.13 | | |
| Q _G | Gate charge | V _{CC} =600 V, I _C =75 A, V _{GE} =15 V | - | 175 | - | nC | |
| t _{d(on)} | Turn-on delay time | V _{CC} =600 V, I _C =75 A, V _{GE} =±15 V, R _G =8.2 Ω, Inductive load | - | - | 300 | ns | |
| t _r | Rise time | | - | - | 200 | | |
| t _{d(off)} | Turn-off delay time | | - | - | 600 | | |
| t _f | Fall time | | - | - | 300 | | |
| V _{EC} ^(Note1) | Emitter-collector voltage | I _E =75 A ^(Note6) , G-E short-circuited, (Terminal) | T _j =25 °C | - | 1.80 | 2.25 | V |
| | | | T _j =125 °C | - | 1.80 | - | |
| | | | T _j =150 °C | - | 1.80 | - | |
| | | I _E =75 A ^(Note6) , G-E short-circuited, (Chip) | T _j =25 °C | - | 1.70 | 2.15 | V |
| | | | T _j =125 °C | - | 1.70 | - | |
| | | | T _j =150 °C | - | 1.70 | - | |
| t _{rr} ^(Note1) | Reverse recovery time | V _{CC} =600 V, I _E =75 A, V _{GE} =±15 V, R _G =8.2 Ω, Inductive load | - | - | 300 | ns | |
| Q _{rr} ^(Note1) | Reverse recovery charge | R _G =8.2 Ω, Inductive load | - | 4.0 | - | μC | |
| E _{on} | Turn-on switching energy per pulse | V _{CC} =600 V, I _C =I _E =75 A, | - | 7.3 | - | mJ | |
| E _{off} | Turn-off switching energy per pulse | V _{GE} =±15 V, R _G =8.2 Ω, T _j =150 °C, | - | 8.0 | - | | |
| E _{rr} ^(Note1) | Reverse recovery energy per pulse | Inductive load | - | 6.9 | - | mJ | |
| R _{CC+EE'} | Internal lead resistance | Main terminals-chip, per switch, T _C =25 °C ^(Note4) | - | - | 4.0 | mΩ | |
| r _g | Internal gate resistance | Per switch | - | 0 | - | Ω | |

BRAKE PART IGBT/DIODE

| Symbol | Item | Conditions | Limits | | | Unit | |
|---------------------|--------------------------------------|---|------------------------|------|------|------|---|
| | | | Min. | Typ. | Max. | | |
| I _{CES} | Collector-emitter cut-off current | V _{CE} =V _{CES} , G-E short-circuited | - | - | 1.0 | mA | |
| I _{GES} | Gate-emitter leakage current | V _{GE} =V _{GES} , C-E short-circuited | - | - | 0.5 | μA | |
| V _{GE(th)} | Gate-emitter threshold voltage | I _C =5 mA, V _{CE} =10 V | 5.4 | 6.0 | 6.6 | V | |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =50 A ^(Note6) , V _{GE} =15 V, (Terminal) | T _j =25 °C | - | 1.80 | 2.25 | V |
| | | | T _j =125 °C | - | 2.00 | - | |
| | | | T _j =150 °C | - | 2.05 | - | |
| | | I _C =50 A ^(Note6) , V _{GE} =15 V, (Chip) | T _j =25 °C | - | 1.70 | 2.15 | V |
| | | | T _j =125 °C | - | 1.90 | - | |
| | | | T _j =150 °C | - | 1.95 | - | |
| C _{ies} | Input capacitance | V _{CE} =10 V, G-E short-circuited | - | - | 5.0 | nF | |
| C _{oes} | Output capacitance | | - | - | 1.0 | | |
| C _{res} | Reverse transfer capacitance | | - | - | 0.08 | | |
| Q _G | Gate charge | V _{CC} =600 V, I _C =50 A, V _{GE} =15 V | - | 117 | - | nC | |

< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

BRAKE PART IGBT/CLAMPDI

| Symbol | Item | Conditions | Limits | | | Unit | |
|---------------------|-------------------------------------|---|------------------------|------|------|------|---|
| | | | Min. | Typ. | Max. | | |
| t _{d(on)} | Turn-on delay time | V _{CC} =600 V, I _C =50 A, V _{GE} =±15 V, R _G =13 Ω, Inductive load | - | - | 300 | ns | |
| t _r | Rise time | | - | - | 200 | | |
| t _{d(off)} | Turn-off delay time | | - | - | 600 | | |
| t _f | Fall time | | - | - | 300 | | |
| I _{RRM} | Reverse current | V _R =V _{RRM} , G-E short-circuited | - | - | 1.0 | mA | |
| V _F | Forward voltage | I _F =50 A ^(Note6) , G-E short-circuited, (Terminal) | T _j =25 °C | - | 1.80 | 2.25 | V |
| | | | T _j =125 °C | - | 1.80 | - | |
| | | | T _j =150 °C | - | 1.80 | - | |
| | | I _F =50 A ^(Note6) , G-E short-circuited, (Chip) | T _j =25 °C | - | 1.70 | 2.15 | V |
| | | | T _j =125 °C | - | 1.70 | - | |
| | | | T _j =150 °C | - | 1.70 | - | |
| t _{rr} | Reverse recovery time | V _{CC} =600 V, I _F =50 A, V _{GE} =±15 V, R _G =13 Ω, Inductive load | - | - | 300 | ns | |
| Q _{rr} | Reverse recovery charge | R _G =13 Ω, Inductive load | - | 2.7 | - | μC | |
| E _{on} | Turn-on switching energy per pulse | V _{CC} =600 V, I _C =I _F =50 A, | - | 5.5 | - | mJ | |
| E _{off} | Turn-off switching energy per pulse | V _{GE} =±15 V, R _G =13 Ω, T _j =150 °C, | - | 5.3 | - | | |
| E _{rr} | Reverse recovery energy per pulse | Inductive load | - | 4.5 | - | | |
| r _g | Internal gate resistance | - | - | 0 | - | Ω | |

CONVERTER PART CONVDI

| Symbol | Item | Conditions | Limits | | | Unit |
|------------------------------|-----------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| I _{RRM} | Reverse current | V _R =V _{RRM} , T _j =150 °C | - | - | 20 | mA |
| V _F (Terminal) | Forward voltage | I _F =75 A ^(Note6) | - | 1.2 | 1.6 | V |

NTC THERMISTOR PART

| Symbol | Item | Conditions | Limits | | | Unit |
|----------------------|-------------------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| R ₂₅ | Zero-power resistance | T _C =25 °C ^(Note4) | 4.85 | 5.00 | 5.15 | kΩ |
| ΔR/R | Deviation of resistance | R ₁₀₀ =493 Ω, T _C =100 °C ^(Note4) | -7.3 | - | +7.8 | % |
| B _(25/50) | B-constant | Approximate by equation ^(Note7) | - | 3375 | - | K |
| P ₂₅ | Power dissipation | T _C =25 °C ^(Note4) | - | - | 10 | mW |

THERMAL RESISTANCE CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|-----------------------|---------------------------------------|---|---|------|------|------|
| | | | Min. | Typ. | Max. | |
| R _{th(j-c)Q} | Thermal resistance ^(Note4) | Junction to case, per Inverter IGBT | - | - | 0.25 | K/W |
| R _{th(j-c)D} | | Junction to case, per Inverter DIODE | - | - | 0.40 | |
| R _{th(j-c)Q} | | Junction to case, per Brake IGBT | - | - | 0.35 | K/W |
| R _{th(j-c)D} | | Junction to case, per Brake CDIODE | - | - | 0.63 | |
| R _{th(j-c)D} | | Junction to case, per Converter DIODE | - | - | 0.24 | K/W |
| R _{th(c-s)} | | Contact thermal resistance ^(Note4) | Case to heat sink, per 1 module, Thermal grease applied ^(Note8) | - | 15 | - |

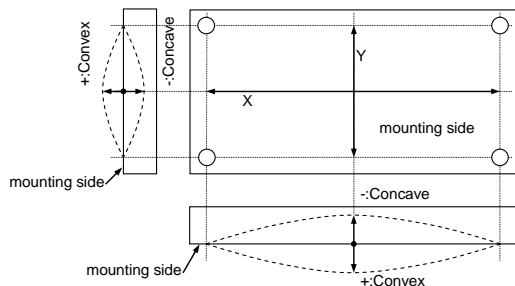
< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).

2. Junction temperature (T_j) should not increase beyond T_{jmax} rating.
3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
4. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
5. The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



6. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

$$7. B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right),$$

R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25}=25 [^{\circ}\text{C}]+273.15=298.15$ [K]

R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50}=50 [^{\circ}\text{C}]+273.15=323.15$ [K]

8. Typical value is measured by using thermally conductive grease of $\lambda=0.9$ W/(m·K).
9. Use the following screws when mounting the printed circuit board (PCB) on the stand offs.
"φ2.6×10 or φ2.6×12 self tapping screw"
The length of the screw depends on the thickness (t1.6~t2.0) of the PCB..

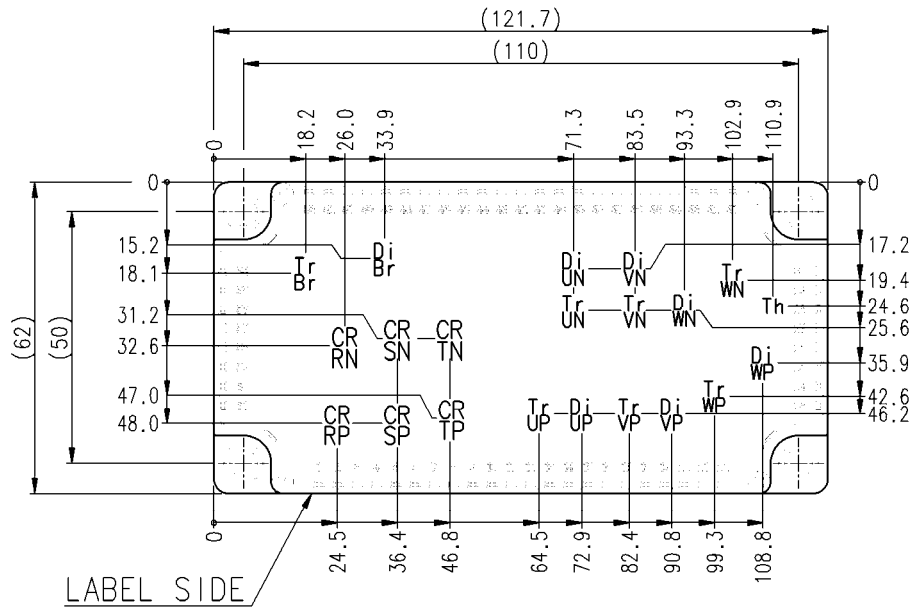
RECOMMENDED OPERATING CONDITIONS

| Symbol | Item | Conditions | Limits | | | Unit |
|------------|-------------------------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| V_{CC} | (DC) Supply voltage | Applied across P-N/P1-N1 terminals | - | 600 | 850 | V |
| V_{GEon} | Gate (-emitter drive) voltage | Applied across GB-Es/ G*P-*/G*N-Es(*=U, V, W) terminals | 13.5 | 15.0 | 16.5 | V |
| R_G | External gate resistance | Per switch | | | | Ω |
| | | Inverter IGBT | 8.2 | - | 82 | |
| | | Brake IGBT | 13 | - | 130 | |

< IGBT MODULES >
CM75MXA-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

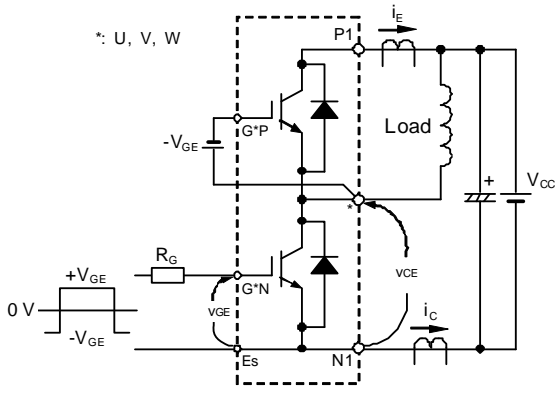
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm

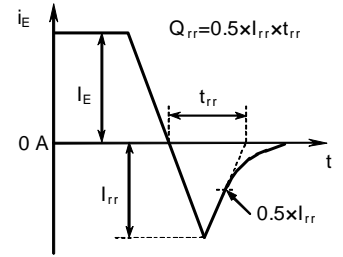
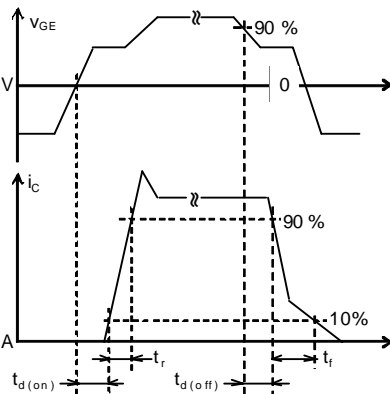


Tr*P/Tr*N/Tr*Br: IGBT, Di*P/Di*N: DIODE (*=U/V/W), Di*Br: BRAKE DIODE, CR*P/CR*N: CONVERTER DIODE (*=R/S/T), Th: NTC thermistor

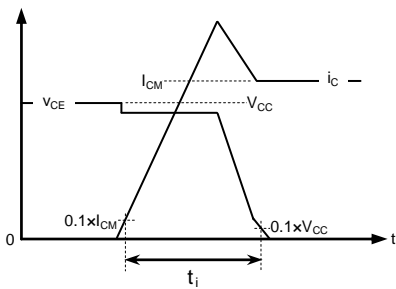
TEST CIRCUIT AND WAVEFORMS



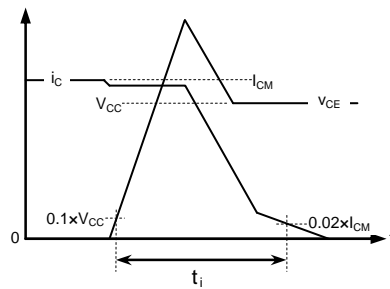
Switching characteristics test circuit and waveforms



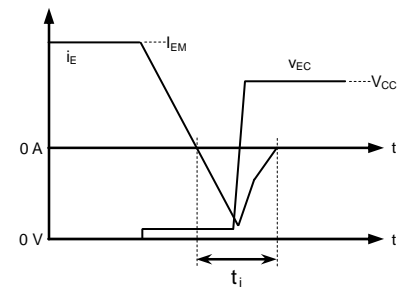
t_{rr}, Q_{rr} test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



DIODE Reverse recovery energy

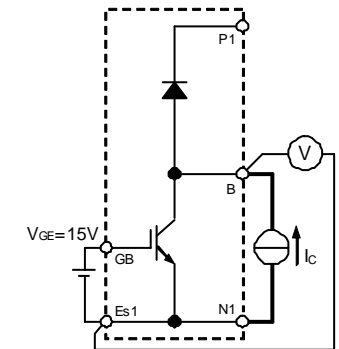
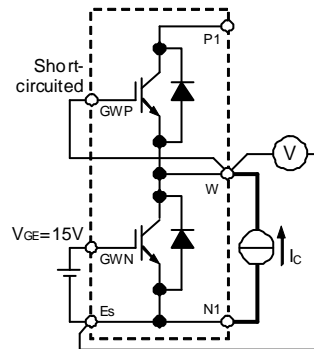
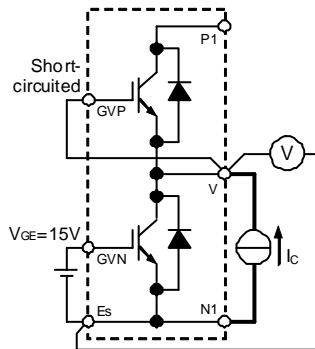
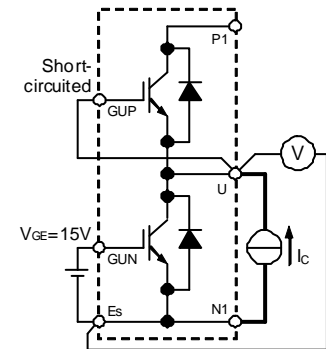
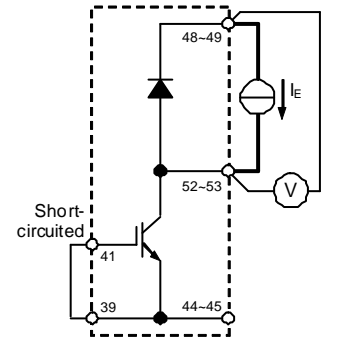
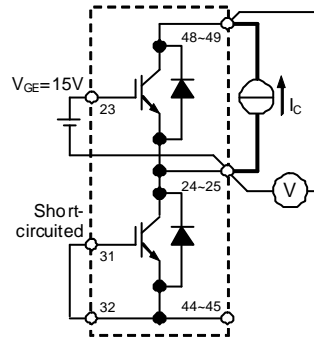
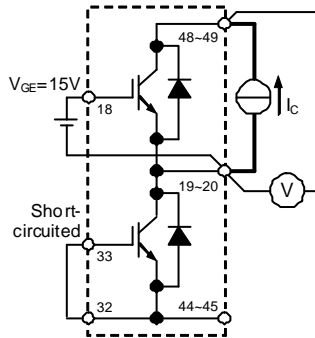
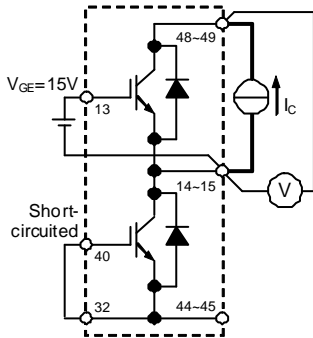
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

< IGBT MODULES >

CM75MXA-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

TEST CIRCUIT



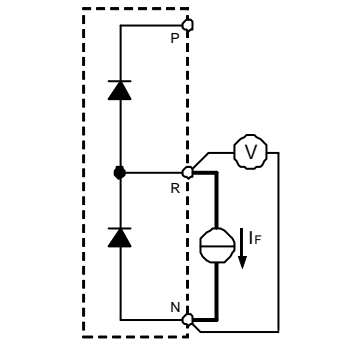
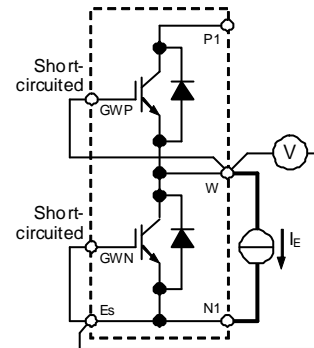
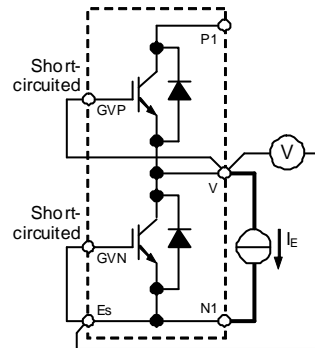
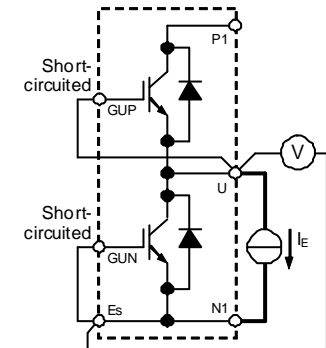
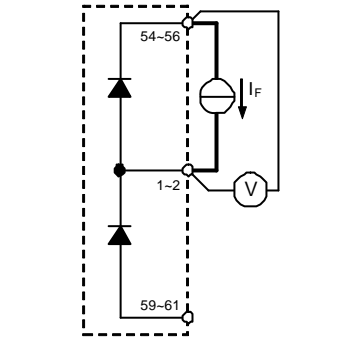
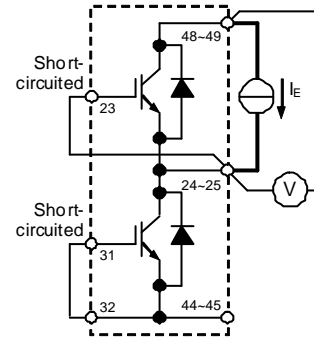
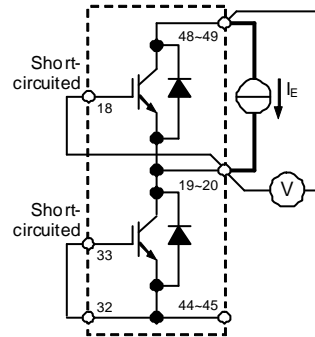
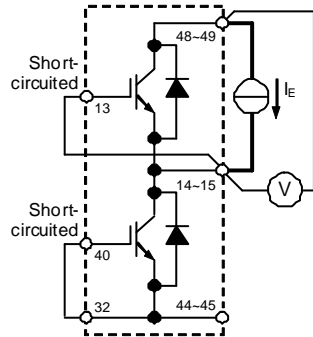
G-E short-circuited
UP / UN IGBT

G-E short-circuited
VP / VN IGBT

G-E short-circuited
WP / WN IGBT

G-E short-circuited
Brake IGBT / DIODE

V_{CEsat} / BRAKE DIODE V_F test circuit



G-E short-circuited
UP / UN DIODE

G-E short-circuited
VP / VN DIODE

G-E short-circuited
WP / WN DIODE

CONVERTER DIODE (ex. phase-R)

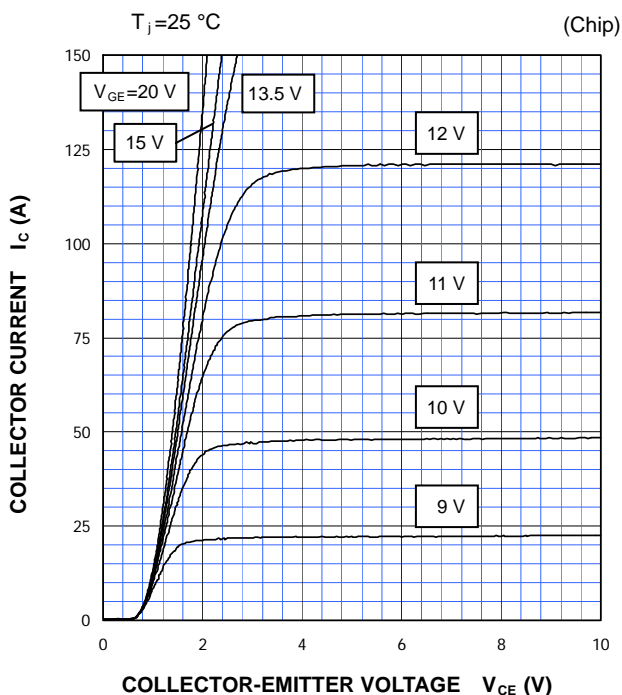
V_{EC} / CONVERTER DIODE V_F test circuit

* In the above test circuit, should use all three main pin terminals (P1/N1/P/N/U/V/W) for connection with the terminals and the current source.

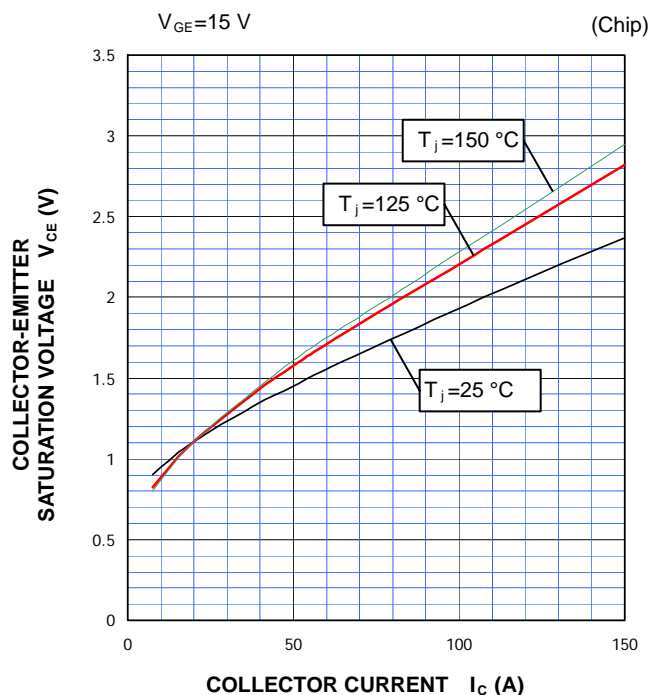
PERFORMANCE CURVES

INVERTER PART

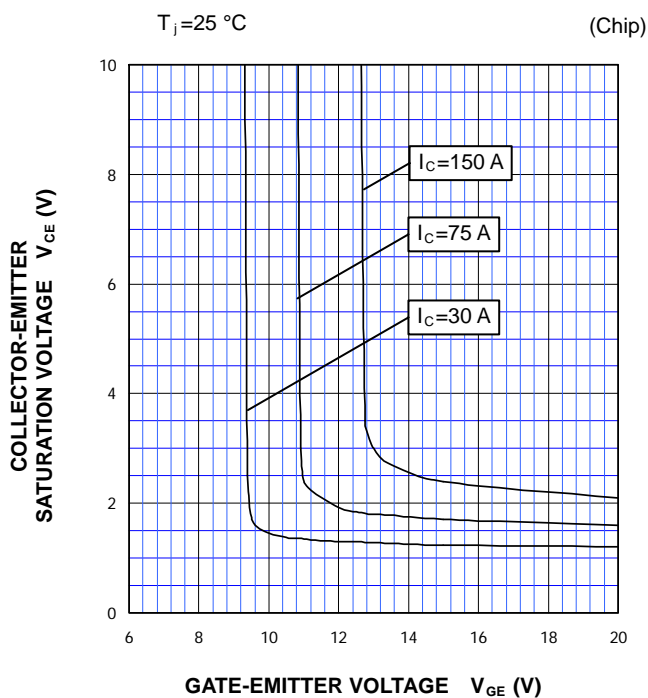
OUTPUT CHARACTERISTICS
(TYPICAL)



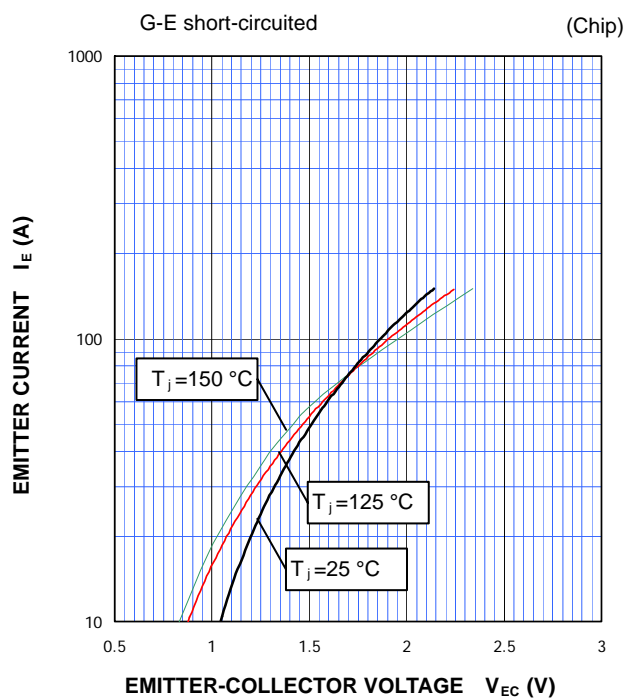
COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)

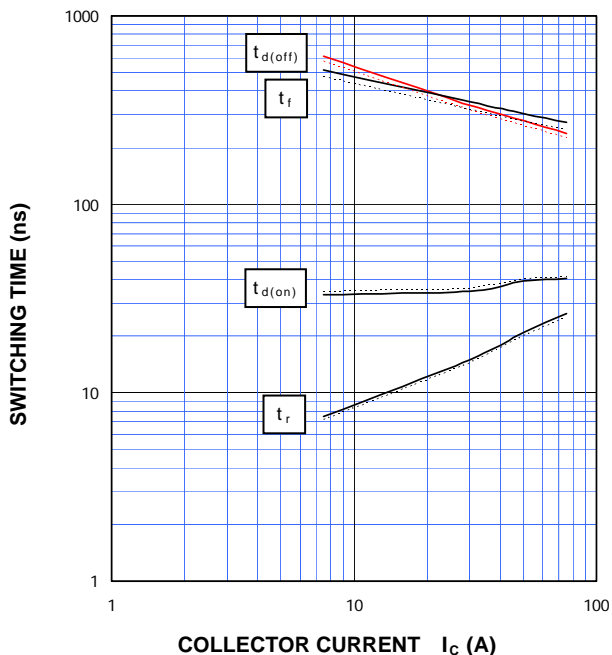


PERFORMANCE CURVES

INVERTER PART

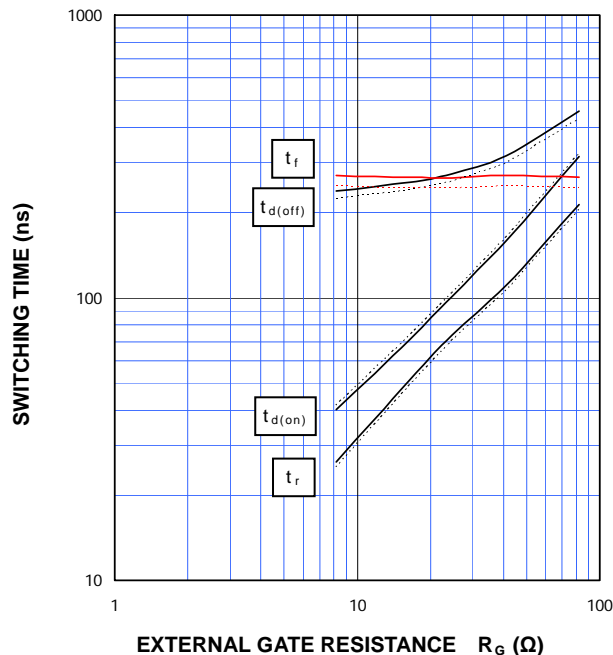
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$, INDUCTIVE LOAD
—: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



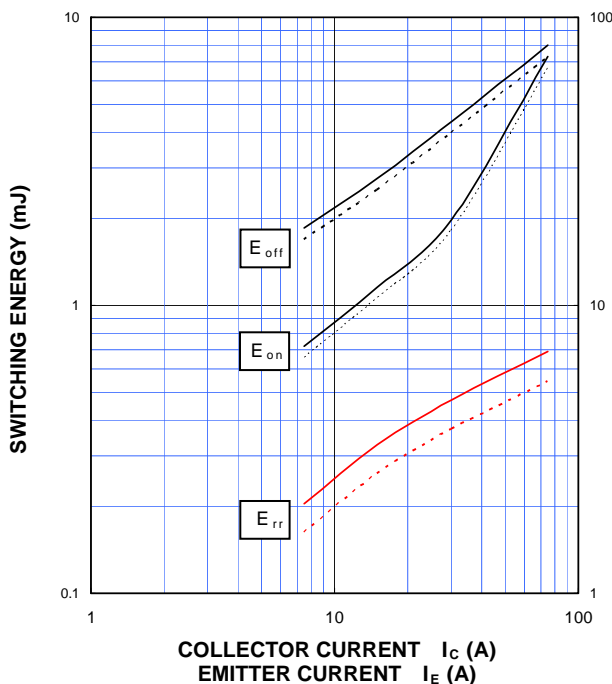
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=75\text{ A}$, INDUCTIVE LOAD
—: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



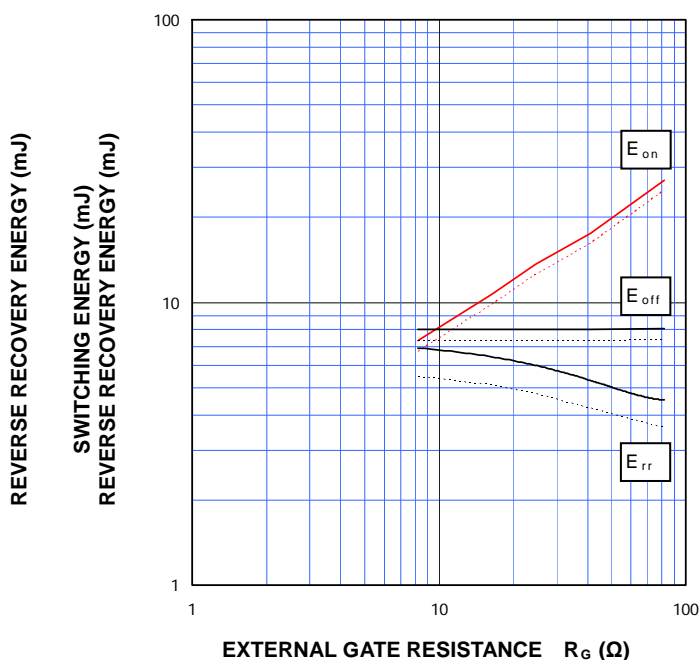
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$,
INDUCTIVE LOAD, PER PULSE
—: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=75\text{ A}$,
INDUCTIVE LOAD, PER PULSE
—: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$

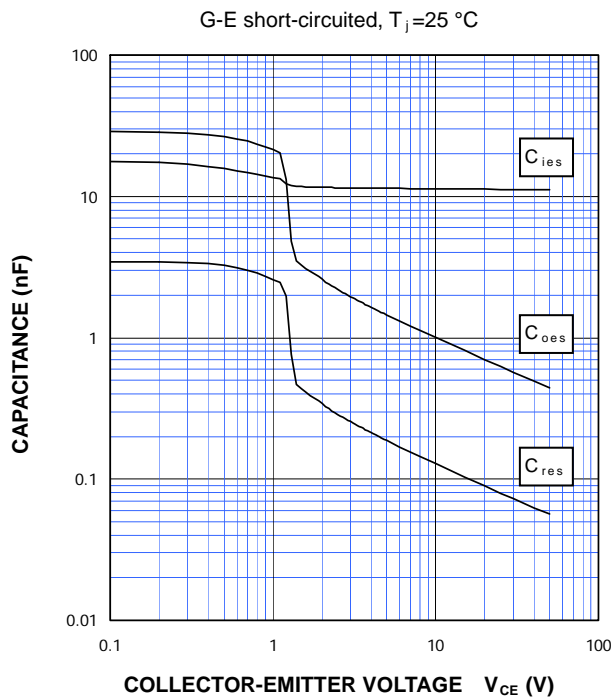


< IGBT MODULES >
CM75MXA-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

PERFORMANCE CURVES

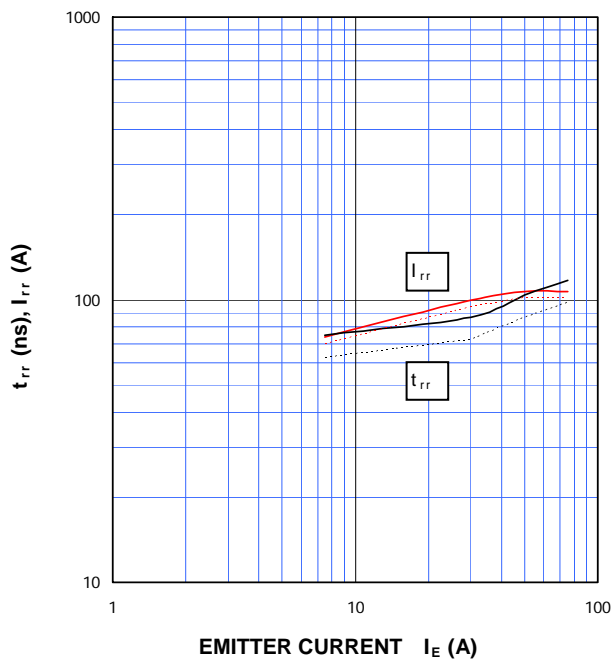
INVERTER PART

CAPACITANCE CHARACTERISTICS (TYPICAL)

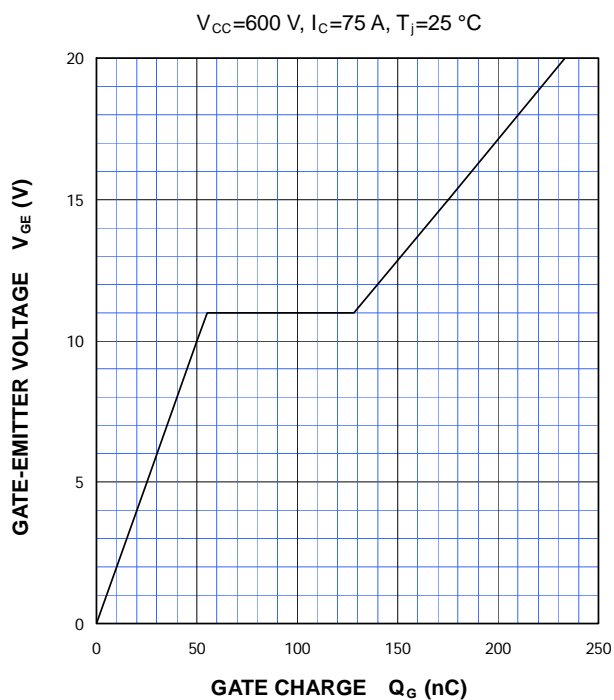


FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$

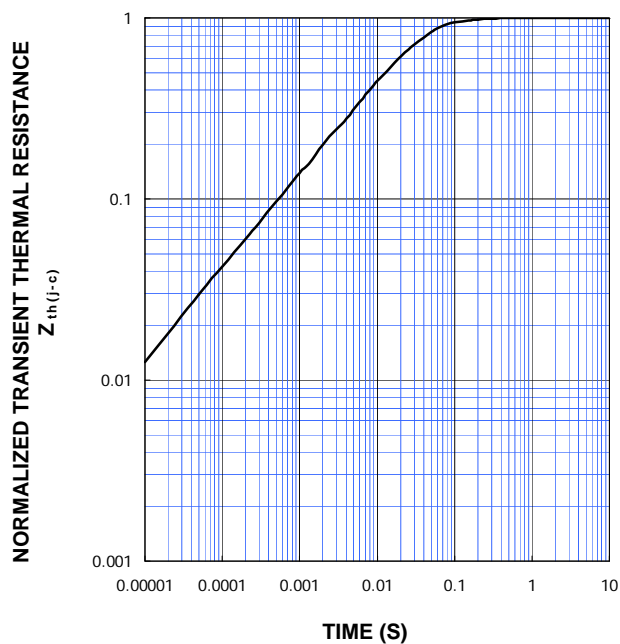


GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

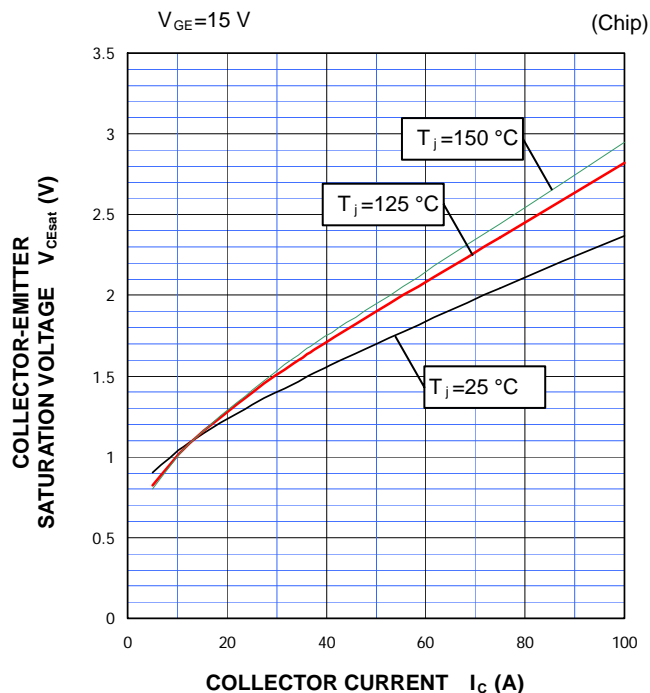
Single pulse, $T_C=25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q}=0.25\text{ K/W}$, $R_{th(j-c)D}=0.40\text{ K/W}$



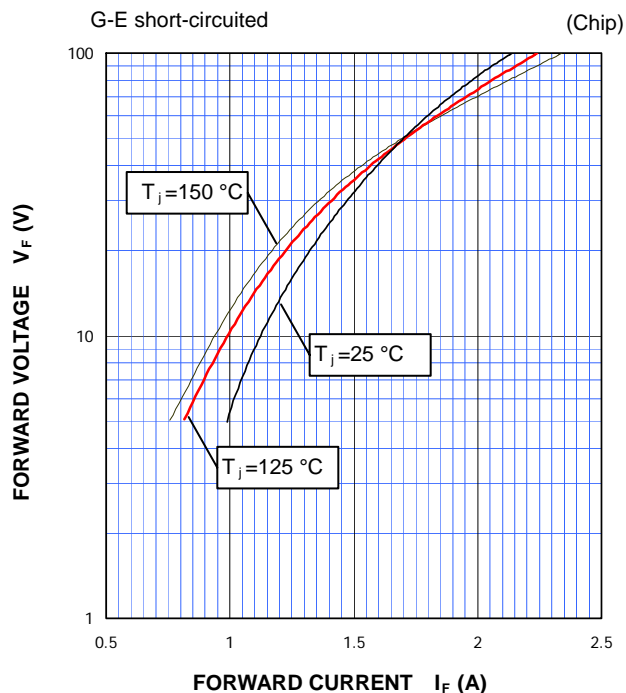
PERFORMANCE CURVES

BRAKE PART

COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)

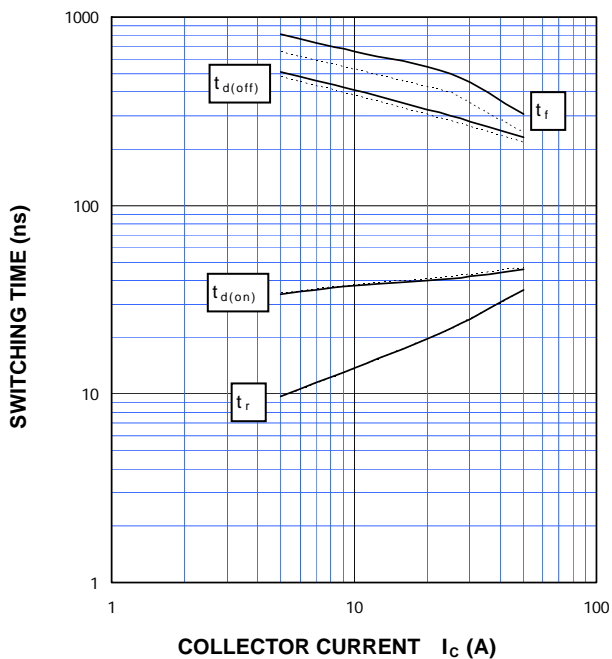


CLAMP DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



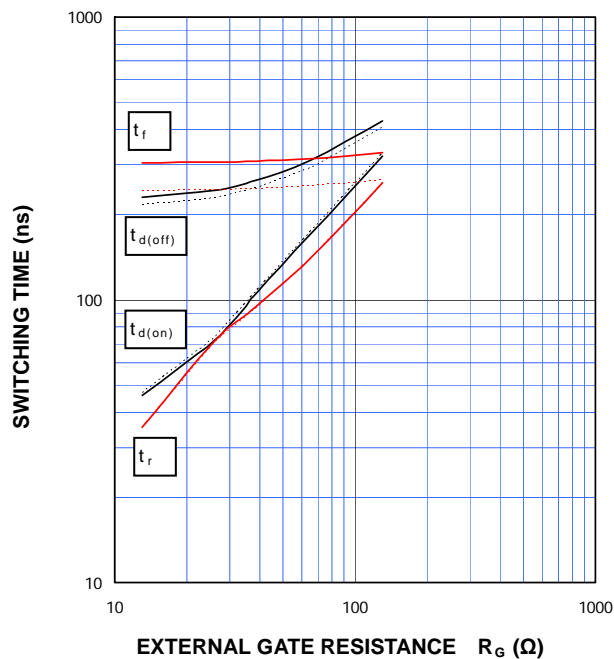
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $R_G = 13 \Omega$, INDUCTIVE LOAD
—: $T_j = 150 \text{ }^\circ\text{C}$, - - - -: $T_j = 125 \text{ }^\circ\text{C}$



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC} = 600 \text{ V}$, $I_C = 50 \text{ A}$, $V_{GE} = \pm 15 \text{ V}$, INDUCTIVE LOAD
—: $T_j = 150 \text{ }^\circ\text{C}$, - - - -: $T_j = 125 \text{ }^\circ\text{C}$

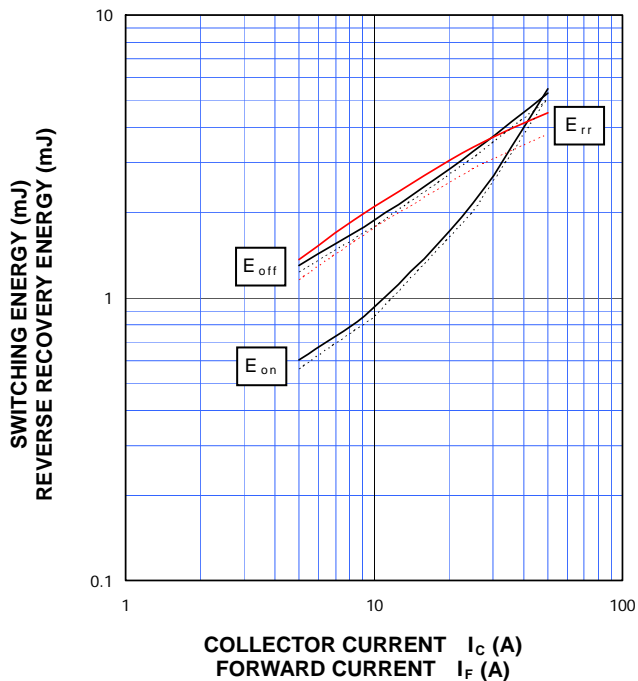


PERFORMANCE CURVES

BRAKE PART

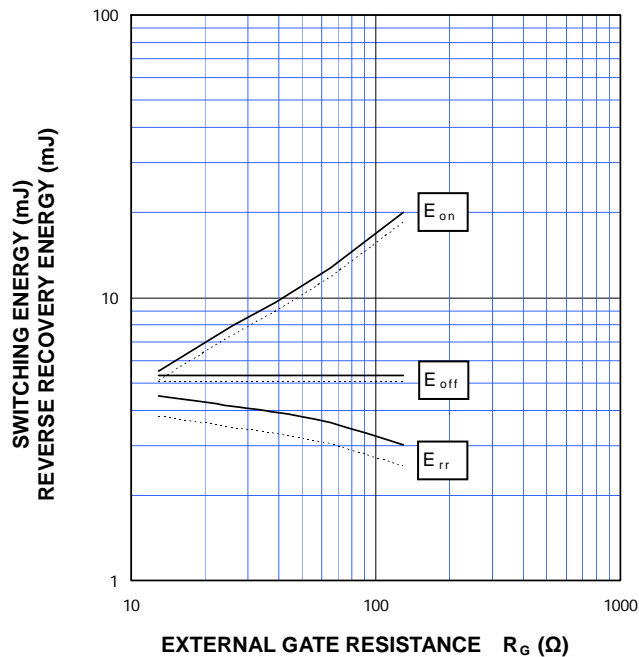
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=13\ \Omega$,
INDUCTIVE LOAD, PER PULSE
—: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



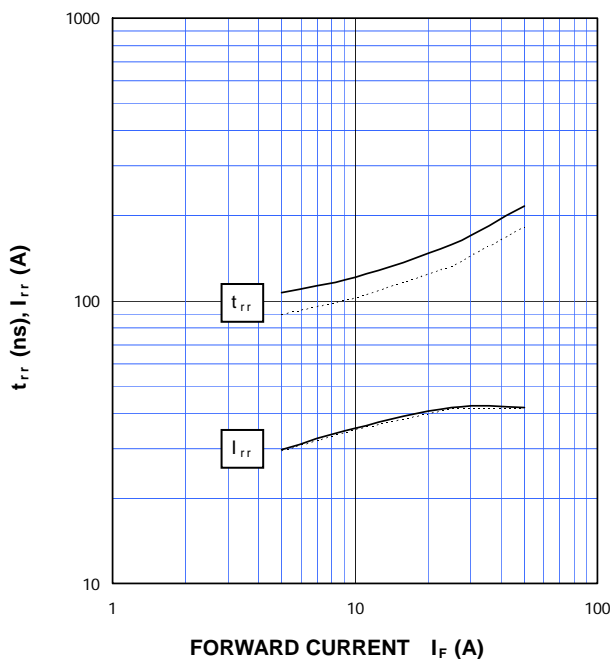
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $I_C/I_F=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
INDUCTIVE LOAD, PER PULSE
—: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



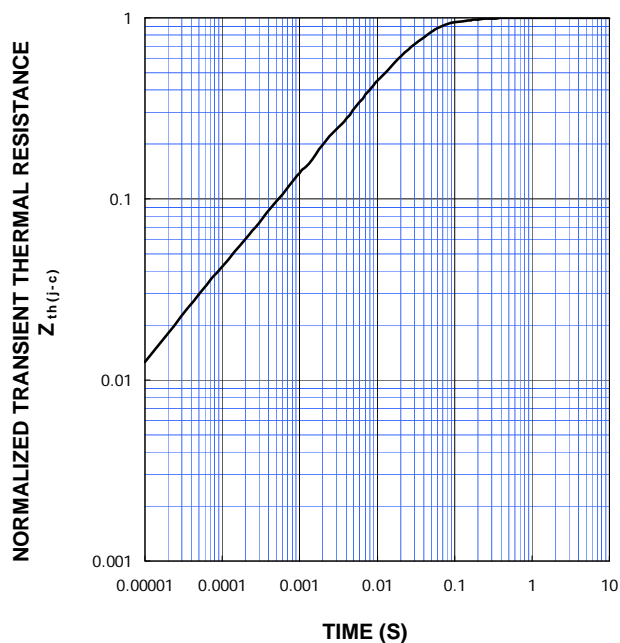
CLAMP DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=13\ \Omega$, INDUCTIVE LOAD
—: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)

Single pulse, $T_C=25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q}=0.35\text{ K/W}$, $R_{th(j-c)D}=0.63\text{ K/W}$

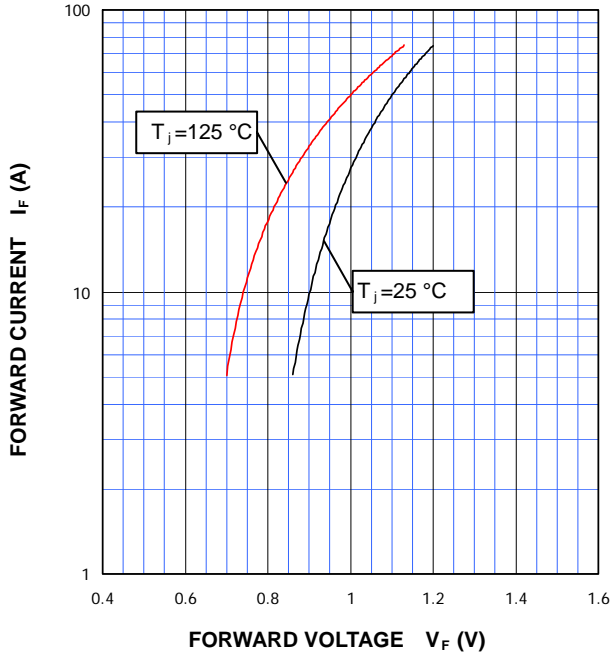


< IGBT MODULES >
CM75MXA-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

PERFORMANCE CURVES

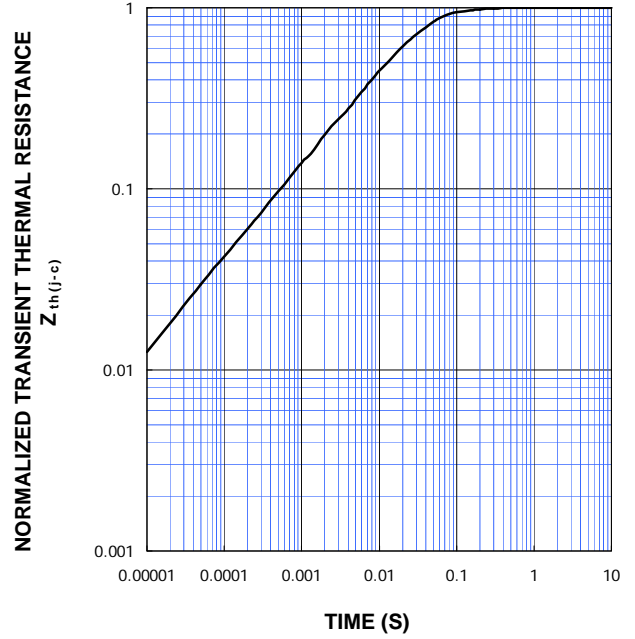
CONVERTER PART

**CONVERTER DIODE
 FORWARD CHARACTERISTICS
 (TYPICAL)**



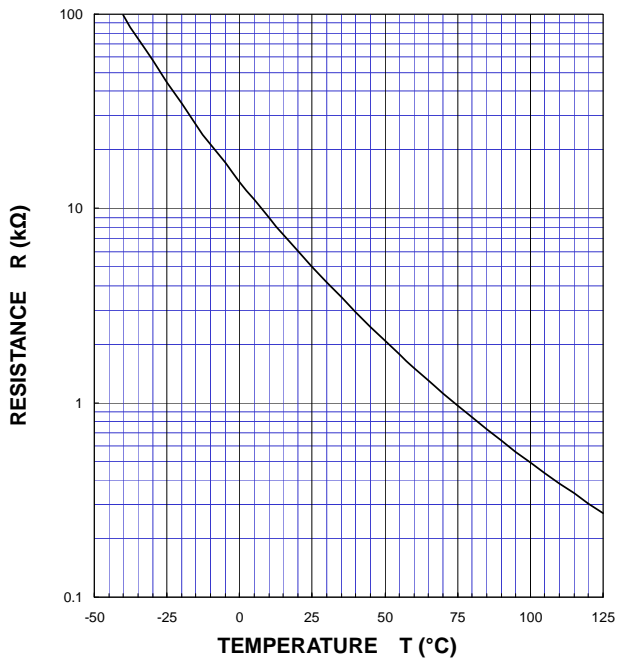
**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
 (MAXIMUM)**

Single pulse, $T_C=25\text{ °C}$
 $R_{th(j-c)D}=0.24\text{ K/W}$



NTC thermistor part

**TEMPERATURE CHARACTERISTICS
 (TYPICAL)**



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